TDA8024AT/C1,112 Datasheet

DiGi Electronics Part Number	TDA8024AT/C1,112-DG
Manufacturer	NXP USA Inc.
Manufacturer Product Number	TDA8024AT/C1,112
Description	IC SMART CARD INTERFACE 28SOIC
Detailed Description	Interface

https://www.DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:

TDA8024AT/C1,112

Manufacturer:

NXP USA Inc.

Series:

*

Product Status:

Obsolete

Base Product Number:

TDA802

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

Moisture Sensitivity Level (MSL):

1 (Unlimited)

REACH Status:

REACH Unaffected

ECCN:

EAR99

HTSUS:

8542.39.0001

TDA8024

Standard smart card interface

Rev. 4.0 — 3 June 2016   **Product data sheet**

1. General description

The TDA8024 is a complete and cost-efficient analog interface for asynchronous 3 V or 5 V smart cards. It can be placed between the card and the microcontroller to perform all supply, protection and control functions. Very few external components are required. The TDA8024AT is a direct replacement for the TDA8004AT.

More information can be obtained from the NXP internet site (www.nxp.com) and from *"Application note AN10141"*.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

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2. Features and benefits

- IC card interface
- 3 V or 5 V supply for the IC (V_{DD} and GND)
- Three specifically protected half-duplex bidirectional buffered I/O lines to card contacts C4, C7 and C8
- DC-to-DC converter for V_{CC} generation separately powered from a 5 V ± 20% supply (V_{DDP} and PGND)
- 3 V or 5 V ± 5% regulated card supply voltage (V_{CC}) with appropriate decoupling has the following capabilities:
  - ◆ I_{CC} < 80 mA at V_{DDP} = 4 V to 6.5 V
  - ◆ Handles current spikes of 40 nAs up to 20 MHz
  - ◆ Controls rise and fall times
  - ◆ Filtered overload detection at approximately 120 mA
- Thermal and short-circuit protection on all card contacts
- Automatic activation and deactivation sequences; initiated by software or by hardware in the event of a short-circuit, card take-off, overheating, V_{DD} or V_{DDP} drop-out
- Enhanced ESD protection on card side (>6 kV)
- 26 MHz integrated crystal oscillator
- Clock generation for cards up to 20 MHz (divided by 1, 2, 4 or 8 through CLKDIV1 and CLKDIV2 signals) with synchronous frequency changes
- Non-inverted control of RST via pin RSTIN
- ISO 7816, GSM11.11 and EMV (payment systems) compatibility

- Supply supervisor for spike-killing during power-on and power-off and Power-on reset (threshold fixed internally or externally by a resistor bridge); not for TDA8024AT
- Built-in debounce on card presence contacts
- One multiplexed status signal $\overline{\text{OFF}}$

3. Applications

- IC card readers for banking
- Electronic payment
- Identification
- Pay TV

4. Quick reference data

Table 1.　Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Power supplies						
V_{DD}	supply voltage		2.7	-	6.5	V
V_{DDP}	DC-to-DC converter supply voltage	V_{CC} = 5 V; $|I_{CC}|$ < 80 mA	4.0	5.0	6.5	V
		V_{CC} = 5 V; $|I_{CC}|$ < 20 mA	3.0	-	6.5	V
I_{DD}	supply current	V_{DD} = 3.3 V; f_{XTAL} = 10 MHz				
		card inactive	-	-	1.2	mA
		card active; $f_{CLK} = f_{XTAL}$; C_L = 30 pF	-	-	1.5	mA
I_{DDP}	DC-to-DC converter supply current	V_{DDP} = 5 V; f_{XTAL} = 10 MHz				
		inactive mode	-	-	0.1	mA
		active mode; $f_{CLK} = f_{XTAL}$; C_L = 30 pF; $|I_{CC}|$ = 0	-	-	10	mA
Card supply						
V_{CC}	card suppy voltage (including ripple voltage)	5 V card:				
		card active; $|I_{CC}|$ < 80 mA DC	4.75	5.0	5.25	V
		card active; current pulses I_p = 40 nAs	4.65	5.0	5.25	V
		3 V card:				
		card active; $|I_{CC}|$ < 65 mA DC	2.85	3.0	3.15	V
		card active; current pulses I_p = 40 nAs	2.76	3.0	3.20	V
$V_{CC(ripple)(p-p)}$	ripple voltage on V_{CC} (peak-to-peak value)	f_{ripple} = 20 kHz to 200 MHz	-	-	350	mV
$|I_{CC}|$	card supply current	V_{CC} = 0 to 5 V	-	-	80	mA
		V_{CC} = 0 to 3 V	-	-	65	mA

Table 1.   Quick reference data *…continued*

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
General							
t_{de}	deactivation time			50	80	100	µs
P_{tot}	total power dissipation	continuous operation; $T_{amb} = -25$ to $+85\ °C$		-	-	0.56	W
T_{amb}	ambient temperature			−25	-	+85	°C

5.   Ordering information

Table 2.   Ordering information

Type number	Package			
	Name	**Description**		**Version**
TDA8024T/C1	SO28	plastic small outline package; 28 leads; body width 7.5 mm		SOT136-1
TDA8024AT/C1	SO28	plastic small outline package; 28 leads; body width 7.5 mm		SOT136-1
TDA8024TT/C1	TSSOP28	plastic thin shrink small outline package; 28 leads; body width 4.4 mm, gold wires		SOT361-1
TDA8024TT/C1/S1	TSSOP28	plastic thin shrink small outline package; 28 leads; body width 4.4 mm, copper wire		SOT361-1

6. Block diagram

(1) Optional external resistor bridge. If this bridge is not required pin 18 should be connected to ground; see Section 8.2.2. Pin 18 is not connected in the TDA8024AT.

Fig 1. Block diagram
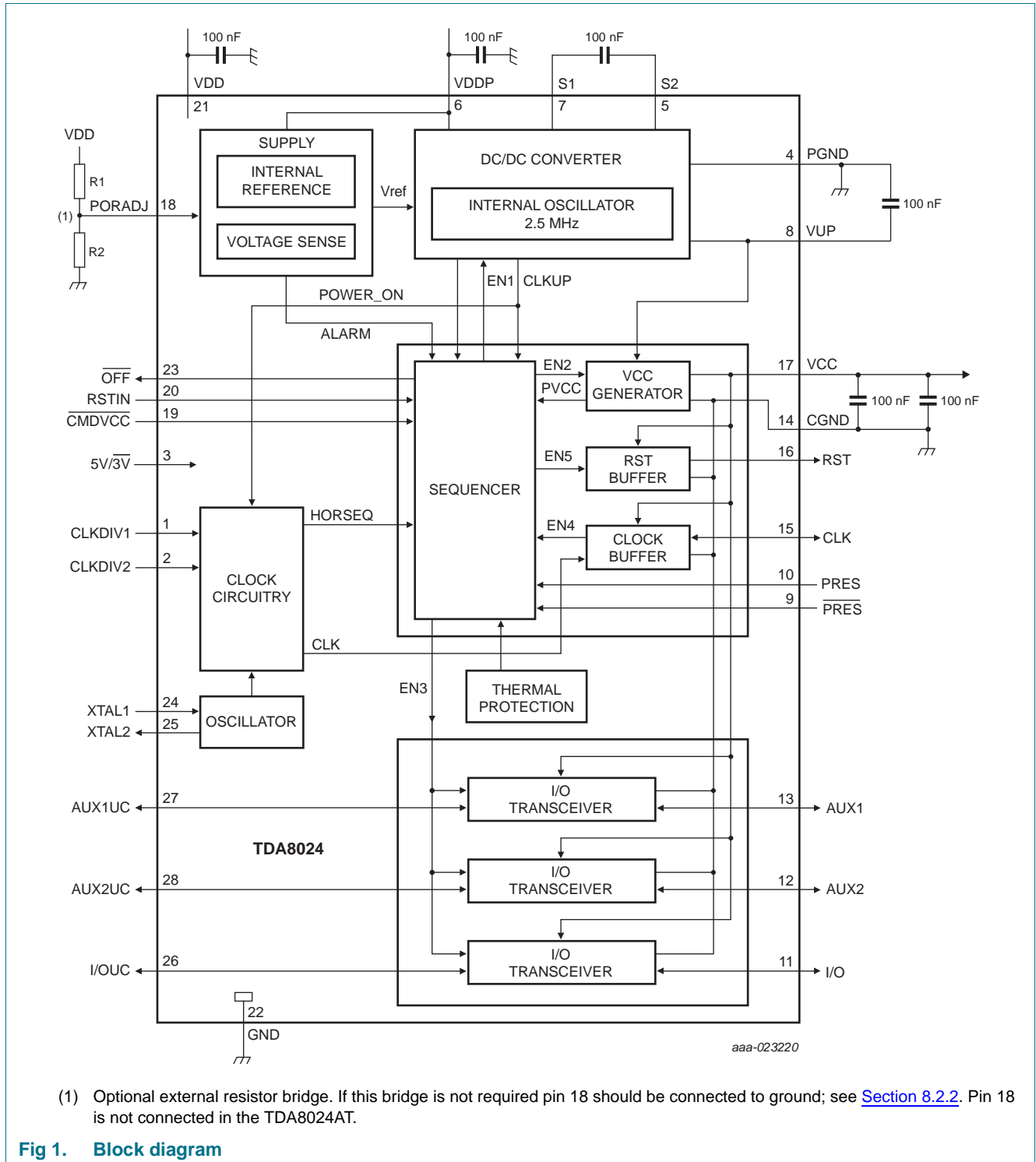
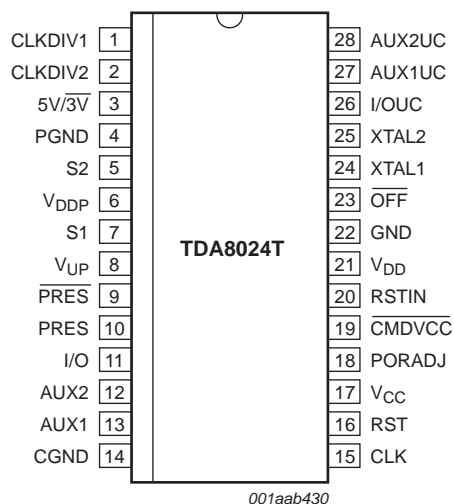# 7. Pinning information

7.1 Pinning

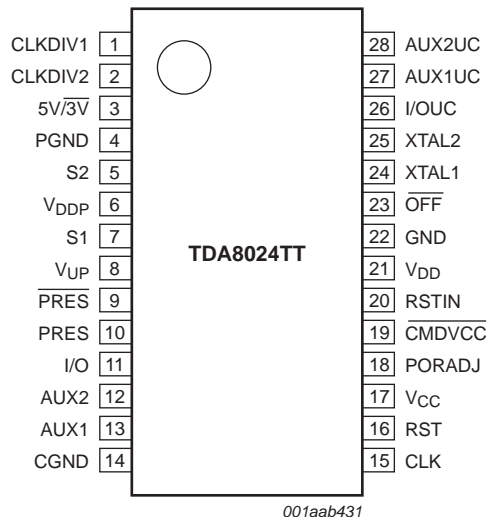

Fig 2. **Pin configuration TDA8024T**
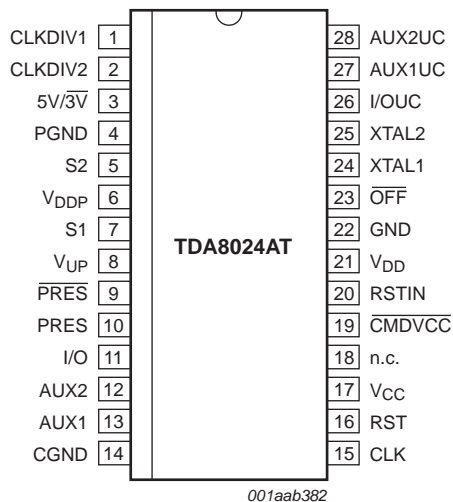

Fig 3. **Pin configuration TDA8024TT**

Fig 4. **Pin configuration TDA8024AT**

7.2 Pin description

Table 3.   Pin description

Symbol	Pin	Type	Description
CLKDIV1	1	I	CLK frequency selection input 1
CLKDIV2	2	I	CLK frequency selection input 2
$5V/\overline{3V}$	3	I	card supply voltage selection input; V_{CC} = 5 V (HIGH) or V_{CC} = 3 V (LOW)
PGND	4	S	DC-to-DC converter power supply ground
S2	5	I/O	DC-to-DC converter capacitor; connected between pins S1 and S2; C = 100 nF with ESR < 100 mΩ
V_{DDP}	6	S	DC-to-DC converter power supply voltage
S1	7	I/O	DC-to-DC converter capacitor; connected between pins S1 and S2; C = 100 nF with ESR < 100 mΩ
V_{UP}	8	I/O	DC-to-DC converter output decoupling capacitor connection; C = 100 nF with ESR < 100 mΩ must be connected between V_{UP} and PGND
$\overline{PRES}$	9	I	card presence contact input (active LOW); if PRES or $\overline{PRES}$ is active, the card is considered 'present' and a built-in debounce feature of 8 ms (typ.) is activated
PRES	10	I	card presence contact input (active HIGH); if PRES or $\overline{PRES}$ is active, the card is considered 'present' and a built-in debounce feature of 8 ms (typ.) is activated
I/O	11	I/O	data line to/from card reader contact C7; integrated 11 kΩ pull-up resistor to V_{CC}
AUX2	12	I/O	data line to/from card reader contact C8; integrated 11 kΩ pull-up resistor to V_{CC}
AUX1	13	I/O	data line to/from card reader contact C4; integrated 11 kΩ pull-up resistor to V_{CC}
CGND	14	S	card signal ground
CLK	15	I/O	card clock to/from card reader contact C3
RST	16	O	card reset output from card reader contact C2
V_{CC}	17	S	card supply voltage to card reader contact C1; decoupled to CGND via 2 × 100 nF or 100 + 220 nF capacitors with ESR < 100 mΩ[1]
PORADJ	18	I	Power-on reset threshold adjustment input for changing the reset threshold with an external resistor bridge; doubles the width of the POR pulse when used; this pin is not connected for the TDA8024AT
$\overline{CMDVCC}$	19	I	input from the host to start activation sequence (active LOW)
RSTIN	20	I	card reset input from the host
V_{DD}	21	S	supply voltage
GND	22	S	ground
$\overline{OFF}$	23	O	NMOS interrupt output to the host (active LOW); 20 kΩ integrated pull-up resistor to V_{DD}
XTAL1	24	I	crystal connection or input for external clock

Table 3. **Pin description** *…continued*

Symbol	Pin	Type	Description
XTAL2	25	O	crystal connection (leave open-circuit if external clock source is used)
I/OUC	26	I/O	host data I/O line; integrated 11 kΩ pull-up resistor to V_{DD}
AUX1UC	27	I/O	auxiliary data line to/from the host; integrated 11 kΩ pull-up resistor to V_{DD}
AUX2UC	28	I/O	

[1] The noise margin on V_{CC} will be higher with the 220 nF capacitor.

8. Functional description

Throughout this document it is assumed that the reader is familiar with ISO7816 terminology.

8.1 Power supply

The supply pins for the IC are V_{DD} and GND. V_{DD} should be in the range of 2.7 V to 6.5 V. All signals interfacing with the system controller are referred to V_{DD}, therefore V_{DD} should also supply the system controller. All card reader contacts remain inactive during power-on or power-off.

The internal circuits are maintained in the reset state until V_{DD} reaches $V_{th2} + V_{hys2}$ and for the duration of the internal Power-on reset pulse, t_W (see Figure 5). When V_{DD} falls below V_{th2}, an automatic deactivation of the contacts is performed.

A DC-to-DC converter is incorporated to generate the 5 V or 3 V card supply voltage (V_{CC}). The DC-to-DC converter should be supplied separately by V_{DDP} and PGND. Due to the possibility of large transient currents, the two 100 nF capacitors of the DC-to-DC converter should be located as near as possible to the IC and have an ESR less than 100 mΩ.

The DC-to-DC converter functions as a voltage doubler or a voltage follower according to the respective values of V_{CC} and V_{DDP} (both have thresholds with a hysteresis of 100 mV).

The DC-to-DC converter function changes as follows.

- V_{CC} = 5 V and V_{DDP} > 5.8 V; voltage follower
- V_{CC} = 5 V and V_{DDP} < 5.7 V; voltage doubler
- V_{CC} = 3 V and V_{DDP} > 4.1 V; voltage follower
- V_{CC} = 3 V and V_{DDP} < 4.0 V; voltage doubler.

Supply voltages V_{DD} and V_{DDP} may be applied to the IC in any sequence.

After powering the device, $\overline{OFF}$ remains LOW until $\overline{CMDVCC}$ is set HIGH.

During power off, $\overline{OFF}$ falls LOW when V_{DD} is below the falling threshold voltage.

8.2 Voltage supervisor

8.2.1 Without external divider on pin PORADJ (or with TDA8024AT)

The voltage supervisor surveys the V_{DD} supply. A defined reset pulse of approximately 8 ms (t_W) is used internally to keep the IC inactive during power-on or power-off of the V_{DD} supply (see Figure 5).

As long as V_{DD} is less than $V_{th2} + V_{hys2}$, the IC remains inactive whatever the levels on the command lines. This state also lasts for the duration of t_W after V_{DD} has reached a level higher than $V_{th2} + V_{hys2}$.

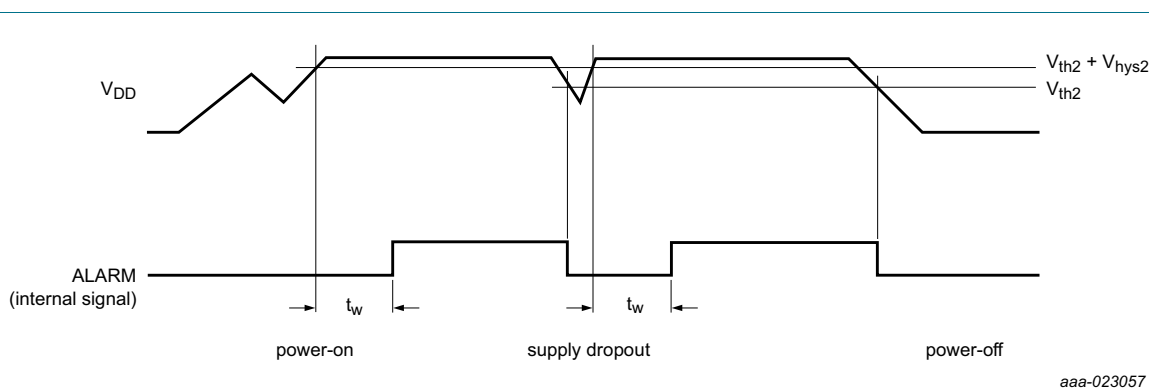When V_{DD} falls below V_{th2}, a deactivation sequence of the contacts is performed.

aaa-023057

Fig 5. **Voltage supervisor**

8.2.2 With an external divider on pin PORADJ (not for the TDA8024AT)

If an external resistor bridge is connected to pin PORADJ (R1 and R2 in Figure 1), then the following occurs:

- The internal threshold voltage V_{th2} is overridden by the external voltage and by the hysteresis, therefore:

$$V_{th2(ext)(rise)} = \left(1 + \frac{R1}{R2}\right) \times \left(V_{bridge} + \frac{V_{hys(ext)}}{2}\right)$$

$$V_{th2(ext)(fall)} = \left(1 + \frac{R1}{R2}\right) \times \left(V_{bridge} - \frac{V_{hys(ext)}}{2}\right)$$

where V_{bridge} = 1.25 V typ. and $V_{hys(ext)}$ = 60 mV typ.

- The reset pulse width t_W is doubled to approximately 16 ms.

Input PORADJ is biased internally with a pull-down current source of 4 μA which is removed when the voltage on pin PORADJ exceeds 1 V. This ensures that after detection of the external bridge by the IC during power-on, the input current on pin PORADJ does not cause inaccuracy of the bridge voltage.

The minimum threshold voltage should be higher than 2 V.

The maximum threshold voltage may be up to V_{DD}.

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TDA8024

8.2.3 Applications examples

The voltage supervisor is used as Power-on reset and as supply dropout detection during a card session.

Supply dropout detection is to ensure that a proper deactivation sequence is followed before the voltage is too low.

For the internal voltage supervisor to function, the system microcontroller should operate down to 2.35 V to ensure a proper deactivation sequence. If this is not possible, external resistor values can be chosen to overcome the problem.

8.2.3.1 Microcontroller requiring a 3.3 V ± 20 % supply

For a microcontroller supplied by 3.3 V with a ±5% regulator and with resistors R1, R2 having a ±1% tolerance, the minimum supply voltage is 3.135 V.

V_{PORADJ} = k × V_{DD}, where $k = \dfrac{S1}{S1 + S2}$ with S1 and S2 the actual values of nominal resistors R1 and R2.

This can be shown as:

0.99 × R1 < S1 < 1.01 × R1 and

0.99 × R2 < S2 < 1.01 × R2

Transposed, this becomes

$$1 + \left(0.98 \times \frac{R1}{R2}\right) \;=\; 1 + \left(\frac{0.99}{1.01}\right) \times \frac{R1}{R2} < \frac{1}{k}$$

$$\frac{1}{k} < 1 + \left(\frac{1.01}{0.99}\right) \times \frac{R1}{R2} \;=\; 1 + \left(1.02 \times \frac{R1}{R2}\right)$$

If V1 = $V_{th(ext)(rise)(max)}$ and V2 = $V_{th(ext)(fall)(min)}$ activation will always be possible if V_{PORADJ} > V1 and deactivation will always be done for V_{PORADJ} < V2.

Activation is always possible for $V_{DD} > \dfrac{V1}{k}$ and deactivation is always possible for $V_{DD} < \dfrac{V2}{k}$

That is V1 = 1.31 V and V2 = 1.19 V and $\dfrac{R1}{R2} < \left(\dfrac{3.135}{1.31} - 1\right) \times 0.98 \;=\; 1.365$

Suppose R1 + R2 = 100 kΩ, then $R2 \;=\; \dfrac{100\,k\Omega}{2.365} \;=\; 42.3\,k\Omega$ and R1 = 57.7 kΩ.

Deactivation will be effective at V2 × (1 + 1.02 × 1.365) = 2.847 V in any case.

If the microcontroller continues to function down to 2.80 V, the slew rate on V_{DD} should be less than 2 V/ms to ensure that clock CLK is correctly delivered to the card until time t_{12} (see Figure 9).

8.2.3.2 Microcontroller requiring a 3.3 V ± 10% supply

For a microcontroller supplied by a 3.3 V with a ±1% regulator and with resistors R1, R2 having a ±0.1% tolerance, the minimum supply voltage is 3.267 V.

The same calculations as in Section 8.2.3.1 conclude:

$$\frac{R1}{R2} < \left(\frac{3.267}{1.310} - 1\right) \times 0.998 = 1.491$$

Therefor $R2 = \frac{100 \ k\Omega}{2.49} = 40.14 \ k\Omega$ and R1 = 59.86 kΩ.

Deactivation will be effective at V2 × (1 + 1.002 × 1.491) = 2.967 V in any case.

If the microcontroller continues to function down to 2.97 V, the slew rate on V_{DD} should be less than 0.20 V/ms to ensure that clock CLK is correctly delivered to the card until time t_{12} (see Figure 9).

8.3 Clock circuitry

The card clock signal (CLK) is derived from a clock signal input to pin XTAL1 or from a crystal operating at up to 26 MHz connected between pins XTAL1 and XTAL2.

The clock frequency can be f_{XTAL}, $\frac{1}{2} \times f_{XTAL}$, $\frac{1}{4} \times f_{XTAL}$ or $\frac{1}{8} \times f_{XTAL}$. Frequency selection is made via inputs CLKDIV1 and CLKDIV2 (see Table 4).

Table 4. Clock frequency selection[1]

CLKDIV1	CLKDIV2	f_{CLK}
0	0	$\frac{f_{XTAL}}{8}$
0	1	$\frac{f_{XTAL}}{4}$
1	1	$\frac{f_{XTAL}}{2}$
1	0	f_{XTAL}

[1] The status of pins CLKDIV1 and CLKDIV2 must not be changed simultaneously; a delay of 10 ns minimum between changes is needed; the minimum duration of any state of CLK is eight periods of XTAL1.

The frequency change is synchronous, which means that during transition no pulse is shorter than 45% of the smallest period, and that the first and last clock pulses about the instant of change have the correct width.

When changing the frequency dynamically, the change is effective for only eight periods of XTAL1 after the command.

The duty factor of f_{XTAL} depends on the signal present at pin XTAL1.

In order to reach a 45% to 55% duty factor on pin CLK, the input signal on pin XTAL1 should have a duty factor of 48% to 52% and transition times of less than 5% of the input signal period.

If a crystal is used, the duty factor on pin CLK may be 45% to 55% depending on the circuit layout and on the crystal characteristics and frequency.

In other cases, the duty factor on pin CLK is guaranteed between 45% and 55% of the clock period.

The crystal oscillator runs as soon as the IC is powered up. If the crystal oscillator is used, or if the clock pulse on pin XTAL1 is permanent, the clock pulse is applied to the card as shown in the activation sequences shown in Figure 7 and 8.

If the signal applied to XTAL1 is controlled by the system microcontroller, the clock pulse will be applied to the card when it is sent by the system microcontroller (after completion of the activation sequence).

8.4 I/O transceivers

The three data lines I/O, AUX1 and AUX2 are identical.

The Idle-state is realized by both I/O and I/OUC lines being pulled HIGH via a 11 kΩ resistor (I/O to V_{CC} and I/OUC to V_{DD}).

Pin I/O is referenced to V_{CC}, and pin I/OUC to V_{DD}, thus allowing operation when V_{CC} is not equal to V_{DD}.

The first side of the transceiver to receive a falling edge becomes the master. An anti-latch circuit disables the detection of falling edges on the line of the other side, which then becomes a slave.
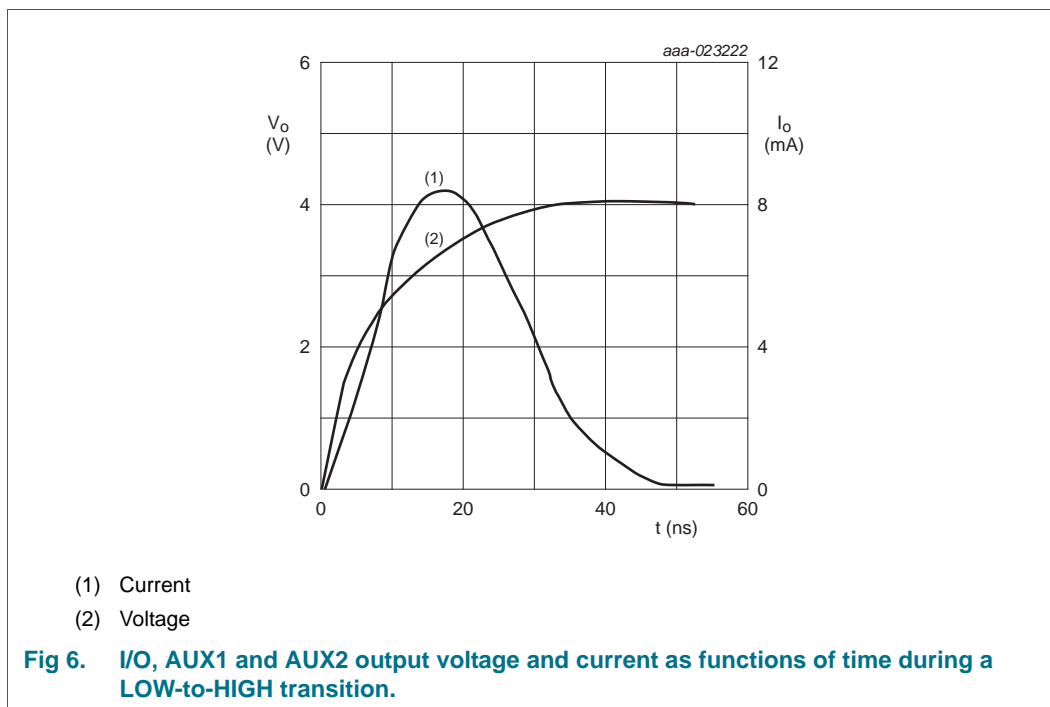
After a time delay $t_{d(edge)}$, an N-transistor on the slave side is turned on, thus transmitting the logic 0 present on the master side.

When the master side returns to logic 1, a P-transistor on the slave side is turned on during the time delay t_{pu} and then both sides return to their idle states.

This active pull-up feature ensures fast LOW-to-HIGH transitions; as shown in Figure 6, it is able to deliver more than 1 mA at an output voltage of up to 0.9V_{CC} into an 80 pF load. At the end of the active pull-up pulse, the output voltage depends only on the internal pull-up resistor and the load current.

The current to and from the card I/O lines is limited internally to 15 mA and the maximum frequency on these lines is 1 MHz.

(1) Current
(2) Voltage

Fig 6.   I/O, AUX1 and AUX2 output voltage and current as functions of time during a LOW-to-HIGH transition.

8.5 Inactive mode

After a Power-on reset, the circuit enters the inactive mode. A minimum number of circuits are active while waiting for the microcontroller to start a session:

- All card contacts are inactive (approximately 200 Ω to GND)
- Pins I/OUC, AUX1UC and AUX2UC are in the high-impedance state (11 kΩ pull-up resistor to V_{DD})
- Voltage generators are stopped
- XTAL oscillator is running
- Voltage supervisor is active
- The internal oscillator is running at its low frequency

8.6 Activation sequence

After power-on and after the internal pulse width delay, the system microcontroller can check the presence of a card using the signals $\overline{OFF}$ and $\overline{CMDVCC}$ as shown in Table 5.

Table 5.   Card presence indication

$\overline{OFF}$	$\overline{CMDVCC}$	Indication
HIGH	HIGH	card present
LOW	HIGH	card not present

If the card is in the reader (this is the case if $\overline{PRES}$ or PRES is active), the system microcontroller can start a card session by pulling $\overline{CMDVCC}$ LOW. The following sequence then occurs (see Figure 6):

1. $\overline{CMDVCC}$ is pulled LOW and the internal oscillator changes to its high frequency (t_0).

2. The voltage doubler is started (between t_0 and t_1).

3. V_{CC} rises from 0 to 5 V (or 3 V) with a controlled slope ($t_2 = t_1 + 1.5 \times T$) where T is 64 times the period of the internal oscillator (approximately 25 μs).

4. I/O, AUX1 and AUX2 are enabled ($t_3 = t_1 + 4T$)

   (these were pulled LOW until this moment).

5. CLK is applied to the C3 contact of the card reader (t_4).

6. RST is enabled ($t_5 = t_1 + 7T$).

The clock may be applied to the card using the following sequence:

1. Set RSTIN HIGH.

2. Set $\overline{\text{CMDVCC}}$ LOW.

3. Reset RSTIN LOW between t_3 and t_5; CLK will start at this moment.

4. RST remains LOW until t_5, when RST is enabled to be the copy of RSTIN.

5. After t_5, RSTIN has no further affect on CLK; this allows a precise count of CLK pulses before toggling RST.

If the applied clock is not needed, then $\overline{\text{CMDVCC}}$ may be set LOW with RSTIN LOW. In this case, CLK will start at t_3 (minimum 200 ns after the transition on I/O), and after t_5, RSTIN may be set HIGH in order to obtain an Answer To Request (ATR) from the card.

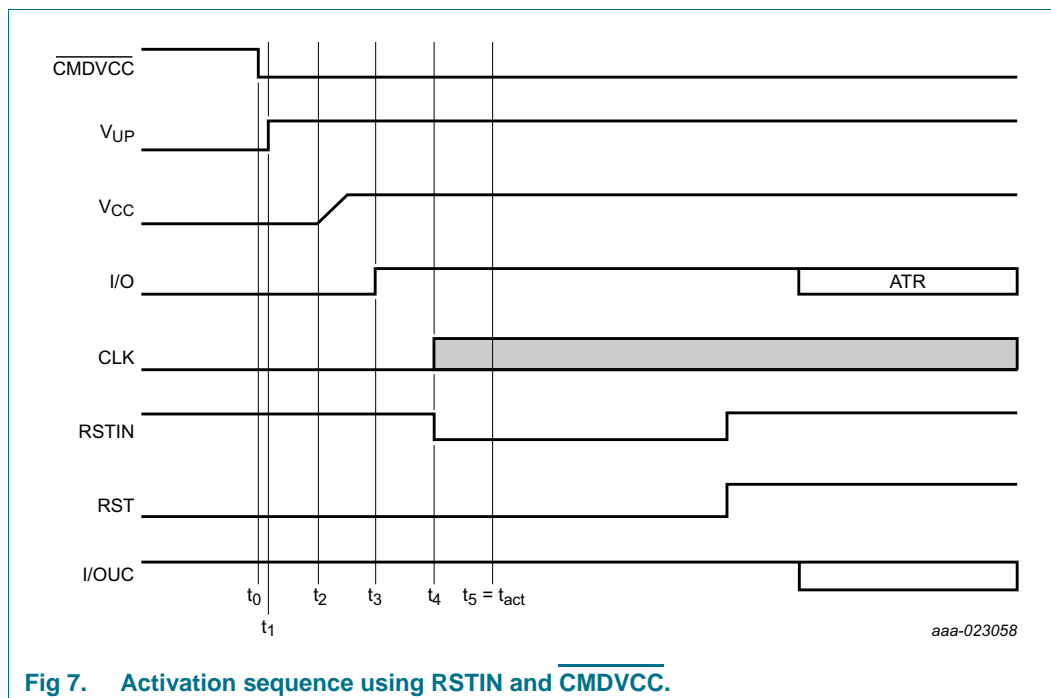Activation should not be performed with RSTIN held permanently HIGH.

Fig 7.   Activation sequence using RSTIN and $\overline{\text{CMDVCC}}$.
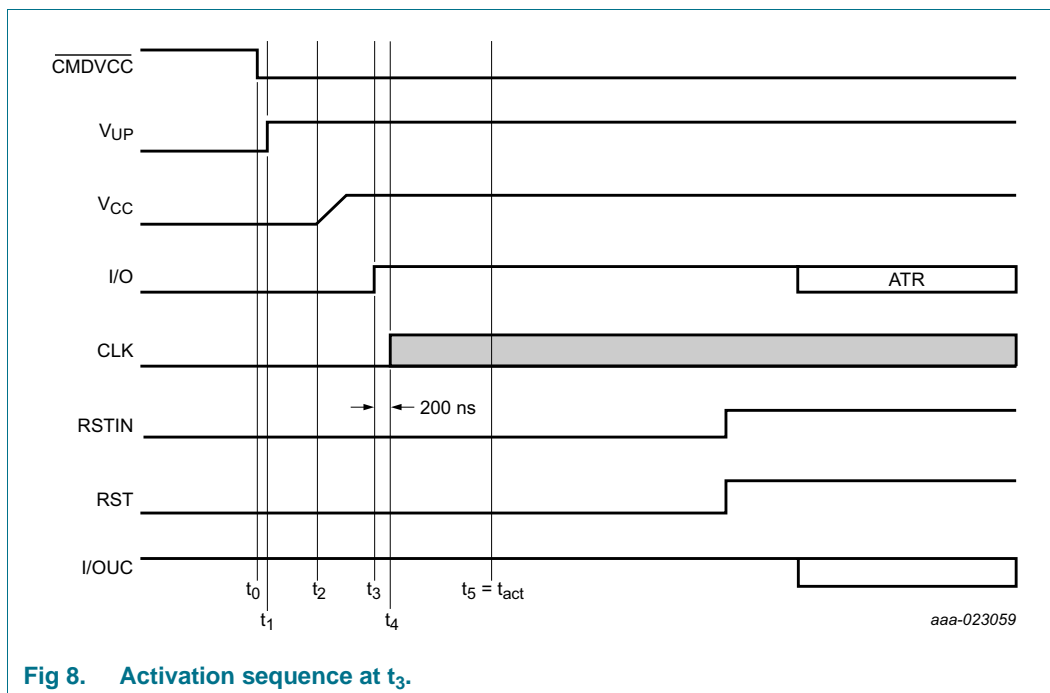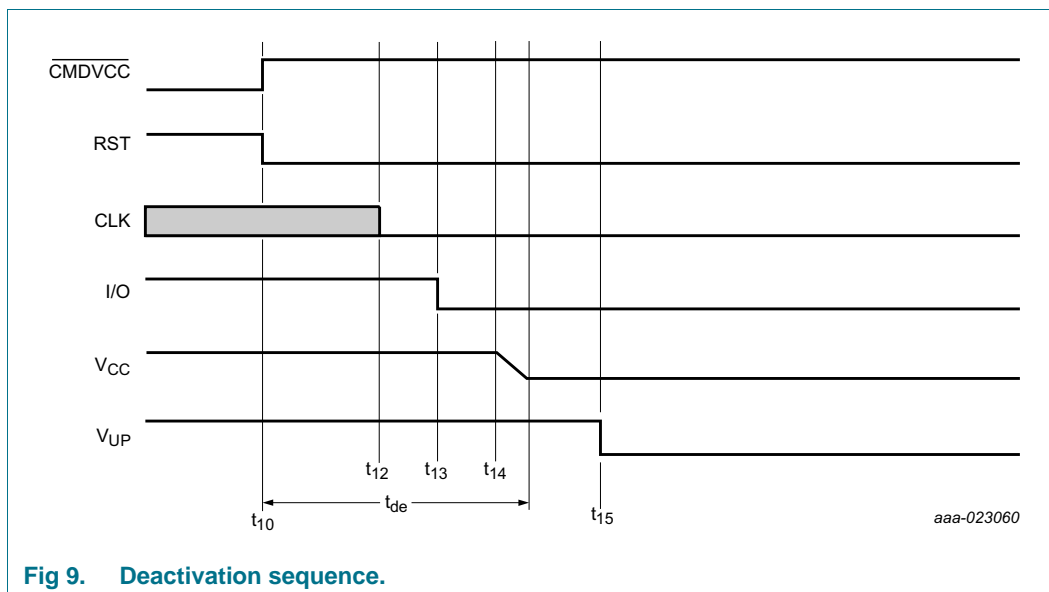
Fig 8. Activation sequence at t_3.

8.7 Active mode

When the activation sequence is completed, the TDA8024 will be in its active mode. Data is exchanged between the card and the microcontroller via the I/O lines. The TDA8024 is designed for cards without V_{PP} (the voltage required to program or erase the internal non-volatile memory).

8.8 Deactive sequence

When a session is completed, the microcontroller sets the $\overline{\text{CMDVCC}}$ line HIGH. The circuit then executes an automatic deactivation sequence by counting the sequencer back and finishing in the inactive mode (see Figure 9):

1. RST goes LOW (t_{10}).

2. CLK is held LOW ($t_{12} = t_{10} + 0.5 \times T$) where T is 64 times the period of the internal oscillator (approximately 25 μs).

3. I/O, AUX1 and AUX2 are pulled LOW ($t_{13} = t_{10} + T$).

4. V_{CC} starts to fall towards zero ($t_{14} = t_{10} + 1.5 \times T$).

5. The deactivation sequence is complete at t_{de}, when V_{CC} reaches its inactive state.

6. V_{UP} falls to zero ($t_{15} = t_{10} + 5T$) and all card contacts become low-impedance to GND; I/OUC, AUX1UC and AUX2UC remain at V_{DD} (pulled-up via a 11 kΩ resistor).

7. The internal oscillator returns to its lower frequency.

TDA8024

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Fig 9. Deactivation sequence.

8.9 V$_{CC}$ generator

The V$_{CC}$ generator has a capacity to supply up to 80 mA continuously at 5 V and 65 mA at 3 V.

An internal overload detector operates at approximately 120 mA. Current samples to the detector are internally filtered, allowing spurious current pulses up to 200 mA with a duration in the order of μs to be drawn by the card without causing deactivation. The average current must stay below the specified maximum current value.

For reasons of V$_{CC}$ voltage accuracy, a 100 nF capacitor with an ESR < 100 mΩ should be tied to CGND near to pin V$_{CC}$, and a 100 nF or 220 nF capacitor (220 nF is the best choice) with the same ESR should be tied to CGND near card reader contact C1.

8.10 Fault detection

The following fault conditions are monitored:

- Short-circuit or high current on V$_{CC}$
- Removal of a card during a transaction
- V$_{DD}$ dropping
- DC-to-DC converter operating out of the specified values (V$_{DDP}$ too low or current from V$_{UP}$ too high)
- Overheating

There are two different cases (see Figure 10):

- $\overline{\text{CMDVCC}}$ **HIGH outside a card session.** Output $\overline{\text{OFF}}$ is LOW if a card is not in the card reader, and HIGH if a card is in the reader. A voltage drop on the V$_{DD}$ supply is detected by the supply supervisor, this generates an internal Power-on reset pulse but does not act upon $\overline{\text{OFF}}$. No short-circuit or overheating is detected because the card is not powered-up.

- $\overline{\text{CMDVCC}}$ **LOW within a card session.** Output $\overline{\text{OFF}}$ goes LOW when a fault condition is detected. As soon as this occurs, an emergency deactivation is performed automatically (see Figure 11). When the system controller resets $\overline{\text{CMDVCC}}$ to HIGH it may sense the $\overline{\text{OFF}}$ level again after completing the deactivation sequence. This distinguishes between a hardware problem or a card extraction ($\overline{\text{OFF}}$ goes HIGH again if a card is present).

Depending on the type of card-present switch within the connector (normally-closed or normally-open) and on the mechanical characteristics of the switch, bouncing may occur on the PRES signals at card insertion or withdrawal.

There is a debounce feature in the device with an 8 ms typical duration (see Figure 10). When a card is inserted, output $\overline{\text{OFF}}$ goes HIGH only at the end of the debounce time.

When the card is extracted, an automatic deactivation sequence of the card is performed on the first true/false transition on PRES or $\overline{\text{PRES}}$ and output $\overline{\text{OFF}}$ goes LOW.

See *"Application note AN10141"* for software decision algorithm on $\overline{\text{OFF}}$ signal.
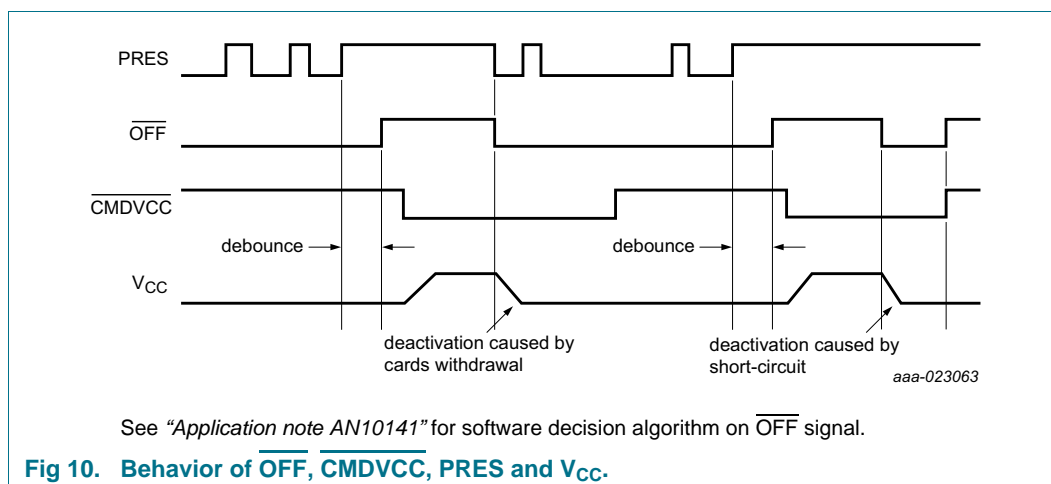
Fig 10. Behavior of $\overline{\text{OFF}}$, $\overline{\text{CMDVCC}}$, PRES and V$_{CC}$.
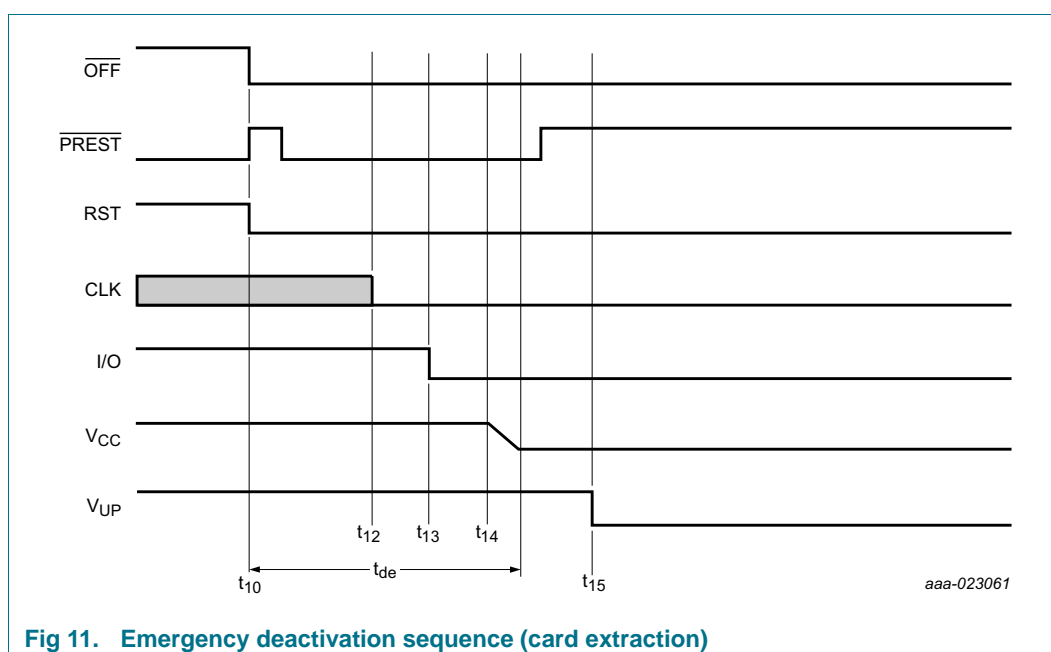

Fig 11. Emergency deactivation sequence (card extraction)

9. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		−0.3	+6.5	V
V_{DDP}	DC-to-DC converter supply voltage		−0.3	+6.5	V
V_I, V_O	voltage on input and output pins	pins XTAL1, XTAL2, 5V/$\overline{3V}$, RSTIN, AUX1UC, $\overline{AUX2UC}$, I/OUC, CLKDIV1, CLKDIV2, $\overline{CMDVCC}$, $\overline{OFF}$ and PORADJ	−0.3	+6.5	V
V_{card}	voltage on card pins	pins PRES, $\overline{PRES}$, I/O, RST, AUX1, AUX2 and CLK	−0.3	+6.5	V
V_n	voltage on other pins	pins V_{UP}, S1 and S2	−0.3	+6.5	V
$T_{j(max)}$	maximum junction temperature		-	150	°C
T_{stg}	storage temperature		−55	+150	°C
V_{ESD}	electrostatic discharge voltage	card contacts in typical application;[1][2]			
		pins I/O, RST, V_{CC}, AUX1, AUX2, CLK, PRES and $\overline{PRES}$	−6	+6	kV
		all pins;[1]			
		Human Body Model (HBM) [2][3]	−2	+2	kV
		Machine Model (MM) [4]	−200	+200	V

[1] All card contacts are protected against any short-circuit with any other card contact.

[2] Every pin withstands the ESD test according to MIL-STD-883C class 3 for card contacts, class 2 for the remaining. Method 3015 (HBM; 1500 Ω and 100 pF) 3 pulses positive and 3 pulses negative on each pin referenced to ground.

[3] In accordance with EIA/JESD22-A114-B, June 2000.

[4] In accordance with EIA/JESD22-A115-A, October 1997.

10. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
	TDA8024T		70	K/W
	TDA8024AT		70	K/W
	TDA8024TT		100[1]	K/W

[1] This figure was obtained using the following Printed-Circuit Board (PCB) technology: FR, 4 layers, 0.5 mm thickness, class 5, copper thickness 35 μm, Ni/Go plating, ground plane in internal layers.

11. Characteristics

Table 8.   **Characteristics**

$V_{DD} = 3.3$ V; $V_{DDP} = 5$ V; $T_{amb} = 25$ ℃; $f_{XTAL} = 10$ MHz; all currents flowing into the IC are positive: see Table note 1; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Temperature						
T_{amb}	ambient temperature		−25	-	+85	°C
Supplies						
V_{DD}	supply voltage		2.7	-	6.5	V
V_{DDP}	DC-to-DC converter supply voltage	$V_{CC} = 5$ V; $|I_{CC}| < 80$ mA	4.0	5.0	6.5	V
		$V_{CC} = 5$ V; $|I_{CC}| < 20$ mA	3.0	-	6.5	V
I_{DD}	supply current	card inactive	-	-	1.2	mA
		card active; $f_{CLK} = f_{XTAL}$; $C_L = 30$ pF	-	-	1.5	mA
I_{DDP}	DC-to-DC converter supply current	inactive mode	-	-	0.1	mA
		active mode; $f_{CLK} = f_{XTAL}$; $C_L = 30$ pF; $|I_{CC}| = 0$	-	-	10	mA
		$V_{CC} = 5$ V; $|I_{CC}| = 80$ mA	-	-	200	mA
		$V_{CC} = 3$ V; $|I_{CC}| = 65$ mA	-	-	100	mA
V_{th2}	falling threshold voltage on V_{DD}	no external resistors at pin PORADJ; V_{DD} level falling	2.35	2.45	2.55	V
V_{hys2}	hysteresis of threshold voltage V_{th2}	no external resistors at pin PORADJ	50	100	150	mV
Pin PORADJ[2]						
$V_{th(ext)(rise)}$	external rising threshold voltage on V_{DD}	external resistor bridge at pin PORADJ; V_{DD} level rising	1.240	1.28	1.310	V
$V_{th(ext)(fall)}$	external falling threshold voltage on V_{DD}	external resistor bridge at pin PORADJ; V_{DD} level falling	1.190	1.22	1.26	V
$V_{hys(ext)}$	hysteresis of threshold voltage $Vt_{h(ext)}$	external resistor bridge at pin PORADJ	30	60	90	mV
$\Delta V_{hys(ext)}$	hysteresis of threshold voltage $V_{th(ext)}$ variation with temperature	external resistor bridge at pin PORADJ	-	-	0.25	mV/K
t_w	width of internal Power-on reset pulse	no external resistors at pin PORADJ	4	8	12	ms
		external resistor bridge at pin PORADJ	8	16	24	ms
$I_{L(PORADJ)}$	leakage current on pin PORADJ	VPORADJ < 0.5 V	−0.1	4	10	μA
		VPORADJ > 1 V	−1	-	+1	μA
P_{tot}	total power dissipation	continuous operation; $T_{amb} = -25$ to $+85$ °C	-	-	0.56	W
DC-to-DC converter						
f_{CLK}	clock frequency	card active	2.2	-	3.2	MHz
$V_{th(vd-vf)}$	threshold voltage for voltage doubler to change to voltage follower	5 V card	5.2	5.8	6.2	V
		3 V card	3.8	4.1	4.4	V

Table 8. **Characteristics** …*continued*

$V_{DD} = 3.3$ V; $V_{DDP} = 5$ V; $T_{amb} = 25$ °C; $f_{XTAL} = 10$ MHz; all currents flowing into the IC are positive: see *Table note 1*; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{UP(av)}$	output voltage on pin V_{UP} (average value)	$V_{CC} = 5$ V	5.2	5.7	6.2	V
		$V_{CC} = 3$ V; $V_{DDP} = 3.3$ V	3.5	3.9	4.3	V
Card supply voltage (pin V_{CC})[3]						
C_{VCC}	external capacitance on pin V_{CC}	[4]	80	-	400	nF
V_{CC}	card supply voltage (including ripple voltage)	5 V card				
		card inactive; $|I_{CC}| = 0$ mA	−0.1	0	+0.1	V
		card inactive; $|I_{CC}| = 1$ mA	−0.1	0	+0.3	V
		card active; $|I_{CC}| < 80$ mA	4.75	5.0	5.25	V
		card active; single current pulse, $I_p = -100$ mA; $t_p = 2$ ms	4.65	5.0	5.25	V
		card active; current pulses, $I_p = 40$ nAs	4.65	5.0	5.25	V
		card active; current pulses, $I_p = 40$ nAs with $|I_{CC}| < 200$ mA; $t_p < 400$ ns	4.65	5.0	5.25	V
		3 V card				
		card inactive; $|I_{CC}| = 0$ mA	−0.1	0	+0.1	V
		card inactive; $|I_{CC}| = 1$ mA	−0.1	0	+0.3	V
		card active; $|I_{CC}| < 65$ mA	2.85	3.0	3.15	V
		card active; single current pulse, $I_p = -100$ mA; $t_p = 2$ ms	2.76	3.0	3.20	V
		card active; current pulses, $I_p = 40$ nAs	2.76	3.0	3.20	V
		card active; current pulses, $I_p = 40$ nAs with $|I_{CC}| < 200$ mA; $t_p < 400$ ns	2.76	3.0	3.20	V
$V_{CC(ripple)(p-p)}$	ripple voltage on V_{CC} (peak to peak value)	$f_{ripple} = 20$ kHz to 200 MHz	-	-	350	mV
$|I_{CC}|$	card supply current	$V_{CC} = 0$ to 5 V	-	-	80	mA
		$V_{CC} = 0$ to 3 V	-	-	65	mA
		V_{CC} short-circuit to GND	100	120	150	mA
SR	slew rate	slew up or down	0.08	0.15	0.22	V/μs
Crystal oscillator (pins XTAL1 and XTAL2)						
C_{XTAL1}, C_{XTAL2}	external capacitance on pins XTAL1 and XTAL2	depends on type of crystal or resonator used	-	-	15	pF
f_{XTAL}	crystal frequency		2	-	26	MHz
f_{XTAL1}	frequency applied on pin XTAL1		0	-	26	MHz
V_{IL}	LOW-level input voltage on pin XTAL1		−0.3	-	+0.3V_{DD}	V

Table 8. **Characteristics** *…continued*

$V_{DD} = 3.3$ V; $V_{DDP} = 5$ V; $T_{amb} = 25$ °C; $f_{XTAL} = 10$ MHz; all currents flowing into the IC are positive: see *Table note 1*; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	HIGH-level input voltage on pin XTAL1		$0.7V_{DD}$	-	$V_{DD} + 0.3$	V
Data lines (pins I/O, I/OUC, AUX1, AUX2, AUX1UC and AUX2UC)						
$t_{d(I/O-I/OUC)}$, $t_{d(I/OUC-I/O)}$	I/O to I/OUC, I/OUC to I/O falling edge delay		-	-	200	ns
t_{pu}	active pull-up pulse width		-	-	100	ns
$f_{I/O(max)}$	maximum frequency on data lines		-	-	1	MHz
C_i	input capacitance on data lines		-	-	10	pF
Data lines to card reader (pins I/O, AUX1 and AUX2; with integrated 11 kΩ pull-up resistors to V_{CC})						
$V_{o(inactive)}$	output voltage	inactive mode				
		no load	0	-	0.1	V
		$I_{o(inactive)} = 1$ mA	-	-	0.3	V
$I_{o(inactive)}$	output current	inactive mode; pin grounded	-	-	−1	mA
V_{OL}	LOW-level output voltage	$I_{OL} = 1$ mA	0	-	0.3	V
		$I_{OL} \geq 15$ mA	$V_{CC} - 0.4$	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	no DC load	$0.9V_{CC}$	-	$V_{CC} + 0.1$	V
		5 V and 3 V cards; $I_{OH} < -40$ µA	$0.75V_{CC}$	-	$V_{CC} + 0.1$	V
		$|I_{OH}| \geq 10$ mA	0	-	0.4	V
V_{IL}	LOW-level input voltage		0.3	-	0.8	V
V_{IH}	HIGH-level input voltage		1.5	-	$V_{CC} + 0.3$	V
$|I_{IL}|$	LOW-level input current	$V_{IL} = 0$ V	-	-	600	µA
$|I_{LIH}|$	HIGH-level input leakage current	$V_{IH} = V_{CC}$	-	-	10	µA
$t_{t(DI)}$	data input transition time	$V_{IL(max)}$ to $V_{IH(min)}$	-	-	1.2	µs
$t_{t(DO)}$	data output transition time	$V_o = 0$ to V_{CC}; $C_L \leq 80$ pF; 10% to 90%	-	-	0.1	µs
R_{pu}	integrated pull-up resistor	pull-up resistor to V_{DD}	9	11	13	kΩ
I_{pu}	current when pull-up active	$V_{OH} = 0.9V_{CC}$; $C = 80$ pF	−1	-	-	mA
Data lines to microcontroller (pins I/OUC, AUX1UC and AUX2UC; with integrated 11 kΩ pull-up resistors to V_{DD})						
V_{OL}	LOW-level output voltage	$I_{OL} = 1$ mA	0	-	0.3	V
V_{OH}	HIGH-level output voltage	no DC load	$0.9V_{DD}$	-	$V_{DD} + 0.1$	V
		5 V and 3 V cards; $I_{OH} < -40$ µA	$0.75V_{DD}$	-	$V_{DD} + 0.1$	V
V_{IL}	LOW-level input voltage		−0.3	-	$+0.3V_{DD}$	V
V_{IH}	HIGH-level input voltage		$0.7V_{DD}$	-	$V_{DD} + 0.3$	V
$|I_{LIH}|$	HIGH-level input leakage current	$V_{IH} = V_{DD}$	-	-	10	µA
$|I_{IL}|$	LOW-level input current	$V_{IL} = 0$ V	-	-	600	µA
$t_{t(DI)}$	data input transition time	$V_{IL(max)}$ to $V_{IH(min)}$	-	-	1.2	µs

Table 8. **Characteristics** *…continued*

V_{DD} = 3.3 V; V_{DDP} = 5 V; T_{amb} = 25 °C; f_{XTAL} = 10 MHz; all currents flowing into the IC are positive: see Table note 1; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{t(DO)}$	data output transition time	V_o = 0 to V_{DD}; C_L < 30 pF; 10% to 90%	-	-	0.1	µs
R_{pu}	integrated pull-up resistor	pull-up resistor to V_{DD}	9	11	13	kΩ
I_{pu}	current when pull-up active	V_{OH} = 0.9V_{DD}; C = 30 pF	−1	-	-	mA
Internal oscillator						
$f_{OSC(int)}$	frequency of internal oscillator	inactive mode	55	140	200	kHz
		active mode	2.2	2.7	3.2	MHz
Reset output to card reader (pin RST)						
$V_{o(inactive)}$	output voltage	inactive mode				
		no load	0	-	0.1	V
		$I_{o(inactive)}$ = 1 mA	0	-	0.3	V
$I_{o(inactive)}$	output current	inactive mode; pin grounded	-	-	−1	mA
$t_{d(RSTIN-RST)}$	RSTIN to RST delay	RST enabled	-	-	2	µs
V_{OL}	LOW-level output voltage	I_{OL} = 200 µA	0	-	0.2	V
		I_{OL} = 20 mA (current limit)	V_{CC} − 0.4	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	I_{OH} = −200 µA	0.9V_{CC}	-	V_{CC}	V
		I_{OH} = −20 mA (current limit)	0	-	0.4	V
t_r	rise time	C_L = 100 pF; V_{CC} = 5 V or 3 V	-	-	0.1	µs
t_f	fall time	C_L = 100 pF; V_{CC} = 5 V or 3 V	-	-	0.1	µs
Clock output to card reader (pin CLK)						
$V_{o(inactive)}$	output voltage	inactive mode				
		no load	0	-	0.1	V
		$I_{o(inactive)}$ = 1 mA	0	-	0.3	V
$I_{o(inactive)}$	output current	CLK inactive; pin grounded	0	-	−1	mA
V_{OL}	LOW-level output voltage	I_{OL} = 200 µA	0	-	0.3	V
		I_{OL} = 70 mA (current limit)	V_{CC} − 0.4	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	I_{OH} = −200 µA	0.9V_{CC}	-	V_{CC}	V
		I_{OH} = −70 mA (current limit)	0	-	0.4	V
t_r	rise time	C_L = 30 pF [5]	-	-	16	ns
t_f	fall time	C_L = 30 pF [5]	-	-	16	ns
δ	duty factor (except for f_{XTAL})	C_L = 30 pF [5]	45	-	55	%
SR	slew rate	slew up or down; C_L = 30 pF	0.2	-	-	V/ns
Control inputs (pins CLKDIV1, CLKDIV2, $\overline{CMDVCC}$, RSTIN and 5V/3V)[6]						
V_{IL}	LOW-level input voltage		−0.3	-	+0.3V_{DD}	V
V_{IH}	HIGH-level input voltage		0.7V_{DD}	-	V_{DD} + 0.3	V
$|I_{LIL}|$	LOW-level input leakage current	0 < V_{IL} < V_{DD}	-	-	1	µA
$|I_{LIH}|$	HIGH-level input leakage current	0 < V_{IH} < V_{DD}	-	-	1	µA

Table 8. **Characteristics** *…continued*

V_{DD} = 3.3 V; V_{DDP} = 5 V; T_{amb} = 25 °C; f_{XTAL} = 10 MHz; all currents flowing into the IC are positive: see Table note 1; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Card presence inputs (pins PRES and $\overline{PRES}$)[7]						
V_{IL}	LOW-level input voltage		−0.3	-	+0.3V_{DD}	V
V_{IH}	HIGH-level input voltage		0.7V_{DD}	-	V_{DD} + 0.3	V
$|I_{LIL}|$	LOW-level input leakage current	0 < V_{IL} < V_{DD}	-	-	5	µA
$|I_{LIH}|$	HIGH-level input leakage current	0 < V_{IH} < V_{DD}	-	-	5	µA
Interrupt output (pin $\overline{OFF}$; NMOS drain with integrated 20 kΩ pull-up resistor to V_{DD})						
V_{OL}	LOW-level output voltage	I_{OL} = 2 mA	0	-	0.3	V
V_{OH}	HIGH-level output voltage	I_{OH} = −15 µA	0.75V_{DD}	-	-	V
R_{pu}	integrated pull-up resistor	20 kΩ pull-up resistor to V_{DD}	16	20	24	kΩ
Protection and limitation						
$|I_{CC(sd)}|$	shutdown and limitation current pin V_{CC}		-	130	150	mA
$I_{I/O(lim)}$	limitation current pins I/O, AUX1 and AUX2		−15	-	+15	mA
$I_{CLK(lim)}$	limitation current pin CLK		−70	-	+70	mA
$I_{RST(lim)}$	limitation current pin RST		−20	-	+20	mA
T_{sd}	shut-down temperature		-	150	-	°C
Timing						
t_{act}	activation time	see Figure 7	50	-	220	µs
t_{de}	deactivation time	see Figure 8	50	80	100	µs
t_3	start of the window for sending CLK to the card	see Figure 7	50	-	130	µs
t_5	end of the window for sending CLK to the card	see Figure 7	140	-	220	µs
$t_{debounce}$	debounce time pins PRES and $\overline{PRES}$	see Figure 10	5	8	11	ms

[1] All parameters remain within limits but are tested only statistically for the temperature range. When a parameter is specified as a function of V_{DD} or V_{CC} it means their actual value at the moment of measurement.

[2] If no external bridge is used then, to avoid any disturbance, it is recommended to connect pin 18 to ground. Pin 18 is not connected in the TDA8024AT.

[3] To meet these specifications, pin V_{CC} should be decoupled to CGND using two ceramic multilayer capacitors of low ESR both with values of 100 nF, or one 100 nF and one 220 nF (see Figure 13).

[4] Permitted capacitor values are 100 nF, or 100 nF + 100 nF, or 220 nF, or 220 nF + 100 nF, or 330 nF.

[5] Transition time and duty factor definitions are shown in Figure 12; $\delta = \dfrac{t_1}{t_1 + t_2}$

[6] Pin $\overline{CMDVCC}$ is active LOW; pin RSTIN is active HIGH; for CLKDIV1 and CLKDIV2 functions see Table 1.

[7] Pin $\overline{PRES}$ is active LOW; pin PRES is active HIGH; PRES has an integrated 1.25 µA current source to GND ($\overline{PRES}$ to V_{DD}); the card is considered present if at least one of the inputs $\overline{PRES}$ or PRES is active.

Fig 12.   Definition of output and input transition times
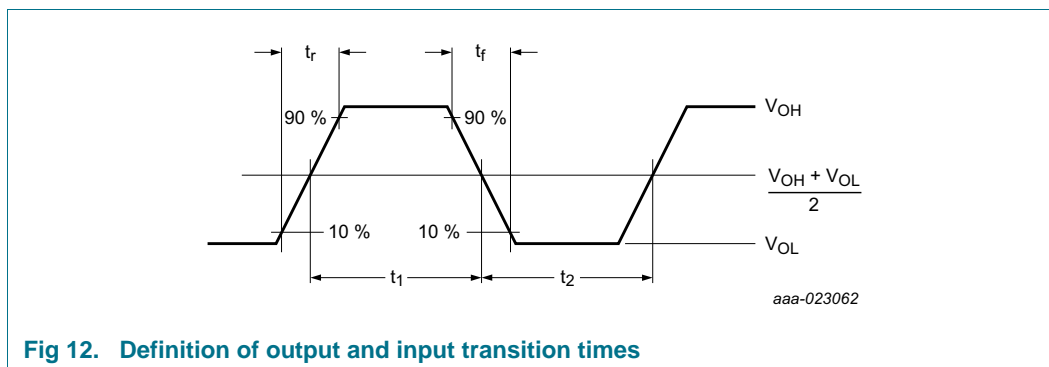
12. Application information

Performance can be affected by the layout of the application. For example, an additional cross-capacitance of 1 pF between card reader contacts C2 and C3 or C2 and C7 can cause contact C2 to be polluted with high frequency noise from C3 (or C7). In this case, include a 100 pF capacitor between contacts C2 and CGND.

Application recommendations:

- Ensure there is ample ground area around the TDA8024 and the connector; place the TDA8024 very near to the connector; decouple the V_{DD} and V_{DDP} lines (these lines are best positioned under the connector)

- The TDA8024 and the microcontroller must use the same V_{DD} supply. Pins CLKDIV1, CLKDIV2, RSTIN, PRES, $\overline{PRES}$, AUX1UC, I/OUC, AUX2UC, 5V/3V, $\overline{CMDVCC}$, and $\overline{OFF}$ are referred to V_{DD}; if pin XTAL1 is to be driven by an external clock, also refer this pin to V_{DD}

- Track C3 should be placed as far as possible from the other tracks

- The track connecting CGND to C5 should be straight (the two capacitors on C1 should be connected to this ground track)

- Avoid ground loops between CGND, PGND and GND

- Decouple V_{DDP} and V_{DD} separately; if the two supplies are the same in the application, then they should be connected in star on the main track.

With all these layout precautions, noise should be kept to an acceptable level and jitter on C3 should be less than 100 ps.

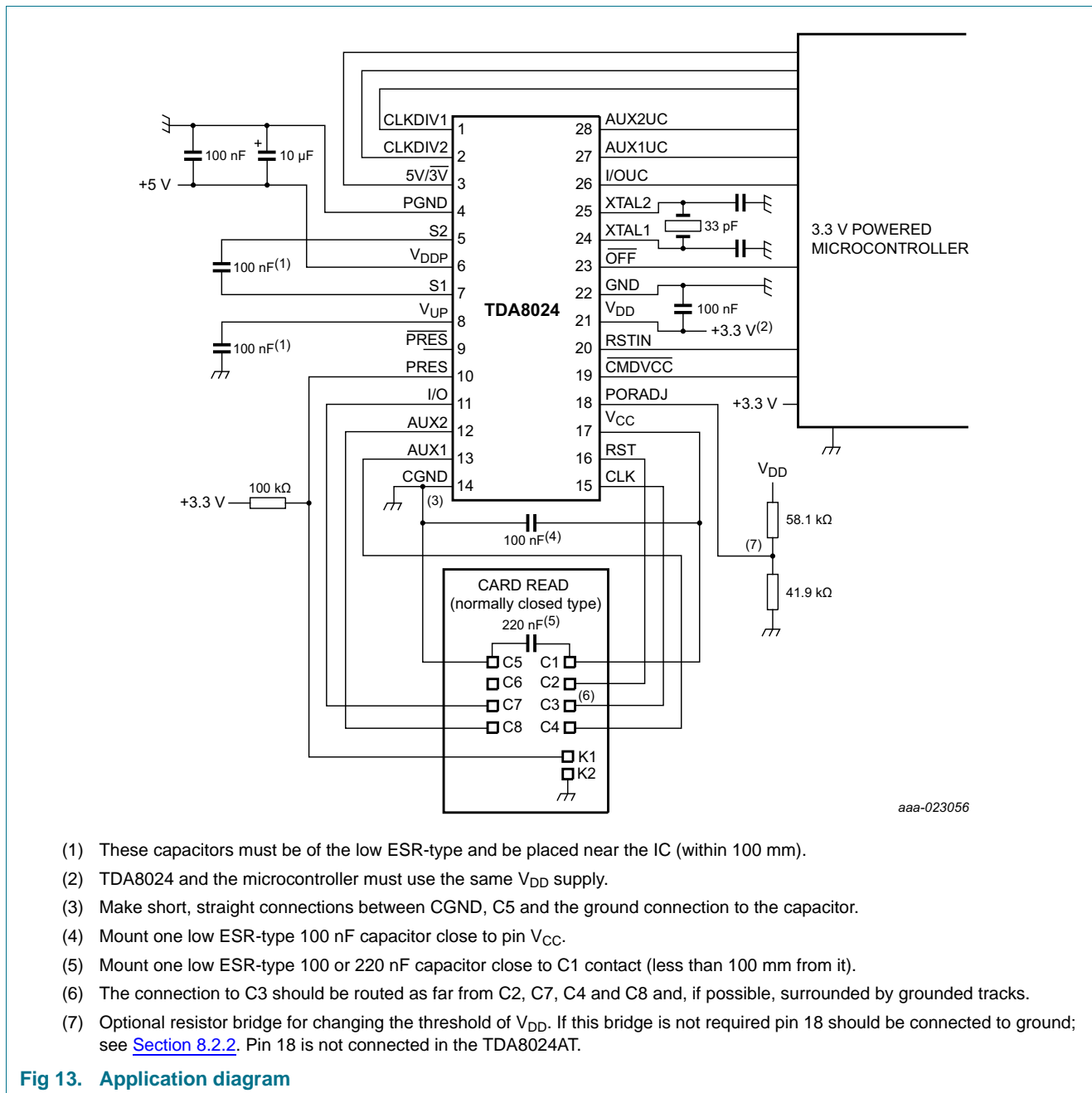Reference layouts are provided in *"Application note 10141"*, available on request.

(1) These capacitors must be of the low ESR-type and be placed near the IC (within 100 mm).

(2) TDA8024 and the microcontroller must use the same V_{DD} supply.

(3) Make short, straight connections between CGND, C5 and the ground connection to the capacitor.

(4) Mount one low ESR-type 100 nF capacitor close to pin V_{CC}.

(5) Mount one low ESR-type 100 or 220 nF capacitor close to C1 contact (less than 100 mm from it).

(6) The connection to C3 should be routed as far from C2, C7, C4 and C8 and, if possible, surrounded by grounded tracks.

(7) Optional resistor bridge for changing the threshold of V_{DD}. If this bridge is not required pin 18 should be connected to ground; see Section 8.2.2. Pin 18 is not connected in the TDA8024AT.

Fig 13. Application diagram

13. Package outline

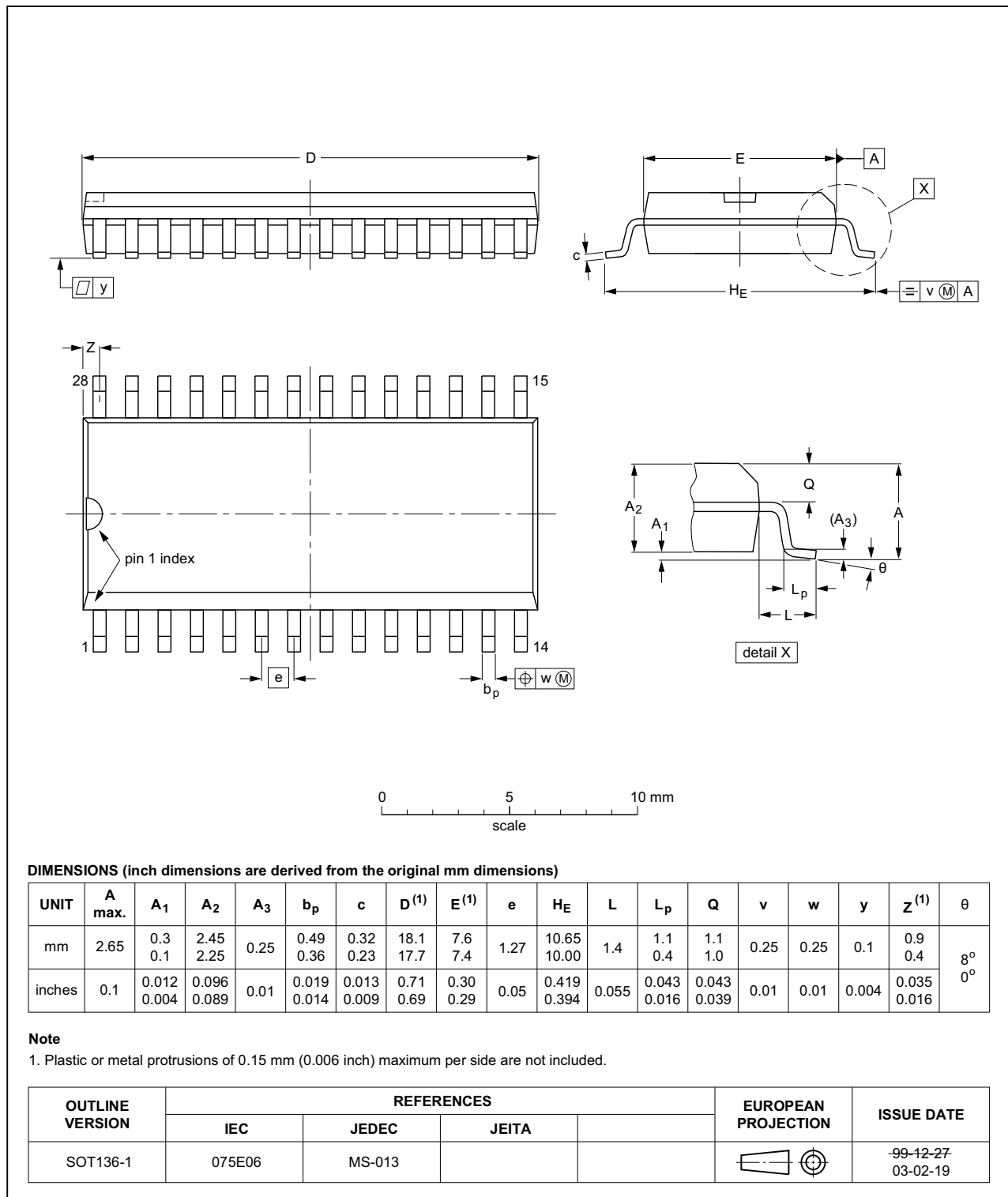**SO28: plastic small outline package; 28 leads; body width 7.5 mm** **SOT136-1**

DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	18.1 17.7	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.71 0.69	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT136-1	075E06	MS-013				~~99-12-27~~ 03-02-19

Fig 14. Package outline SOT136-1 (SO28)

TSSOP28: plastic thin shrink small outline package; 28 leads; body width 4.4 mm　　　**SOT361-1**

DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A₁	A₂	A₃	b_P	c	D [1]	E [2]	e	H_E	L	L_p	Q	v	w	y	Z [1]	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	9.8 9.6	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.8 0.5	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT361-1		MO-153				~~99-12-27~~ 03-02-19

Fig 15.　Package outline SOT361-1 (TSSOP28)

14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

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14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see Figure 16) than a SnPb process, thus reducing the process window

- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board

- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 9 and 10

Table 9.   SnPb eutectic process (from J-STD-020D)

Package thickness (mm)	Package reflow temperature (°C)	
	Volume (mm^3)	
	< 350	≥ 350
< 2.5	235	220
≥ 2.5	220	220

Table 10.   Lead-free process (from J-STD-020D)

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm^3)		
	< 350	350 to 2000	> 2000
< 1.6	260	260	260
1.6 to 2.5	260	250	245
> 2.5	250	245	245

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 16.

MSL: Moisture Sensitivity Level

Fig 16. Temperature profiles for large and small components
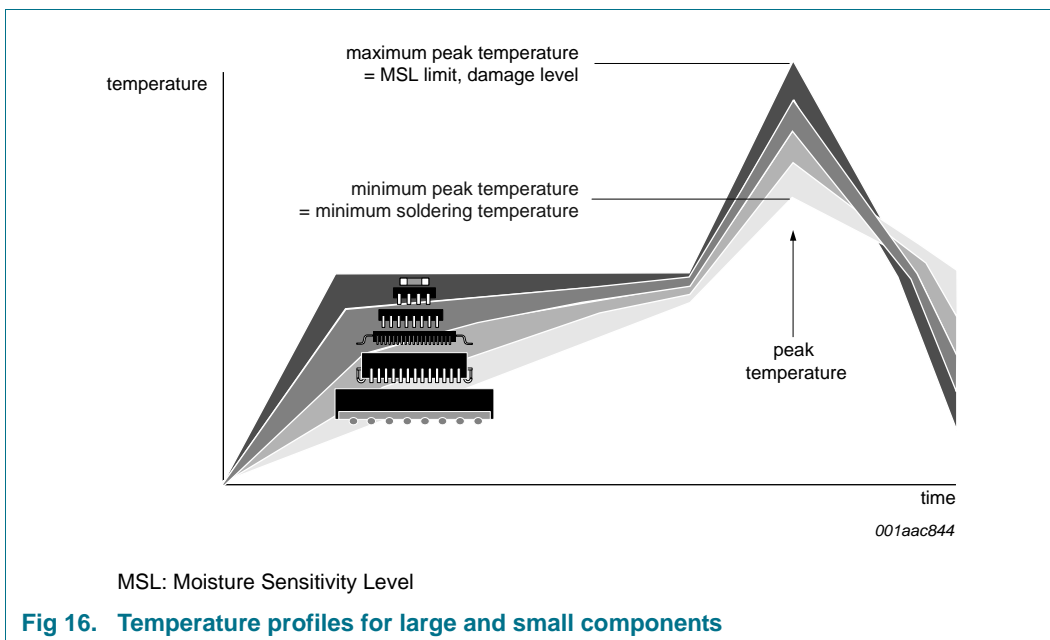
For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

15. Revision history

Table 11.   Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TDA8024 v.4.0	20160603	Product data sheet	-	TDA8024_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 5 "Ordering information": updated			
TDA8024_3	20040712	Product specification	-	TDA8024_2
TDA8024_2	20030819	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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TDA8024

Standard smart card interface

18. Contents

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